

ZXTN25040DFH

40V, SOT23, NPN medium power transistor

Summary

$BV_{CEX} > 130V$

$BV_{CEO} > 40V$

$BV_{ECO} > 6V$

$I_{C(cont)} = 4A$

$V_{CE(sat)} < 55\text{ mV @ } 1A$

$R_{CE(sat)} = 35\text{ m}\Omega$

$P_D = 1.25W$

Complementary part number ZXTP25040DFH

Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

Features

- High power dissipation SOT23 package
- High peak current
- High gain
- Low saturation voltage
- 130V forward blocking voltage
- 6V reverse blocking voltage

Applications

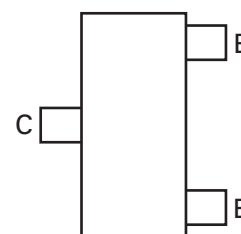
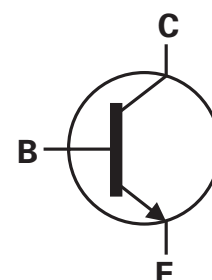
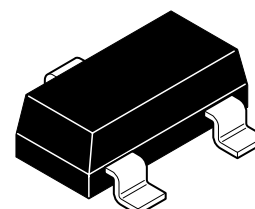
- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25040DFHTA	7	8	3,000

Device marking

1A4



Pinout - top view

ZXTN25040DFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	130	V
Collector-emitter voltage (forward blocking)	V_{CEX}	130	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	6	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current ^(c)	I_C	4	A
Base current	I_B	1	A
Peak pulse current	I_{CM}	10	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P_D	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$	P_D	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	P_D	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

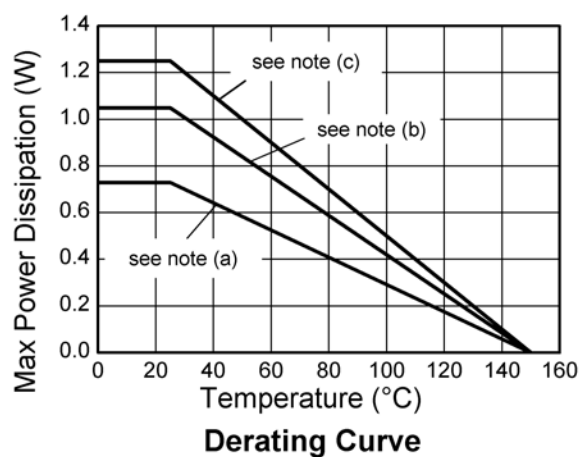
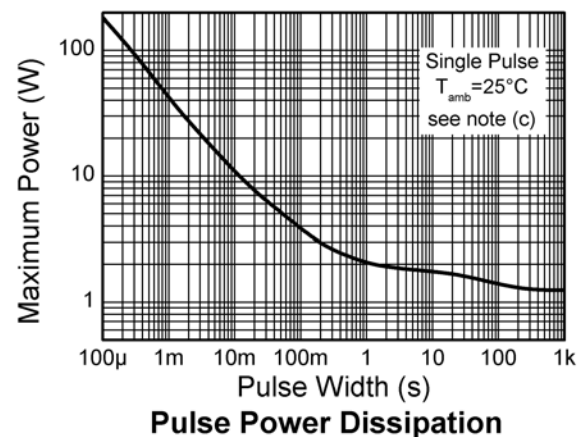
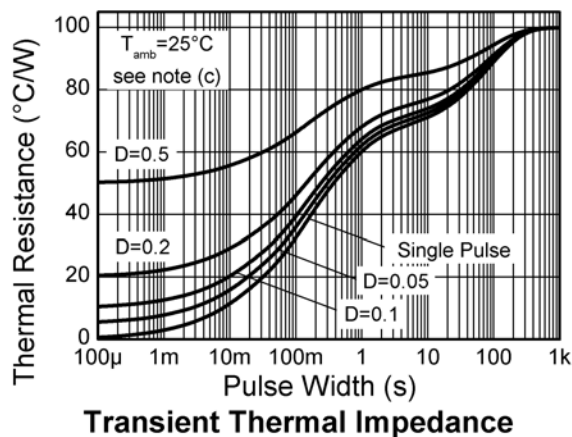
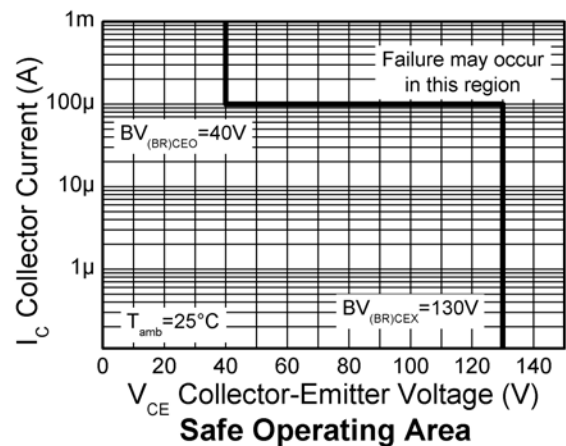
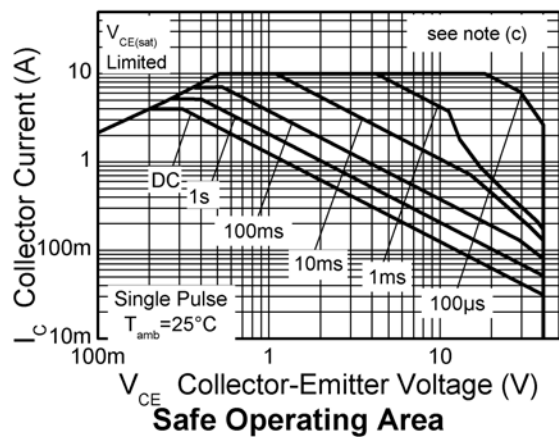
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

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Characteristics



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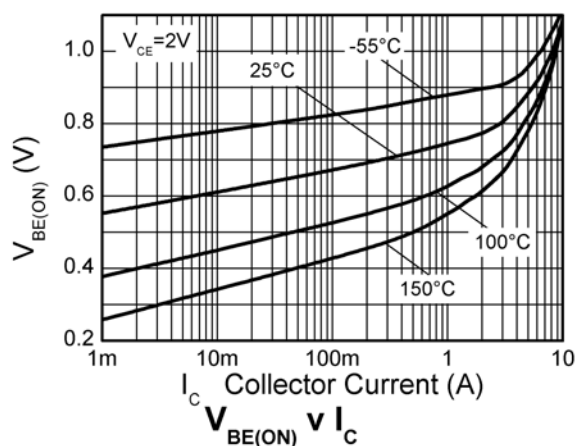
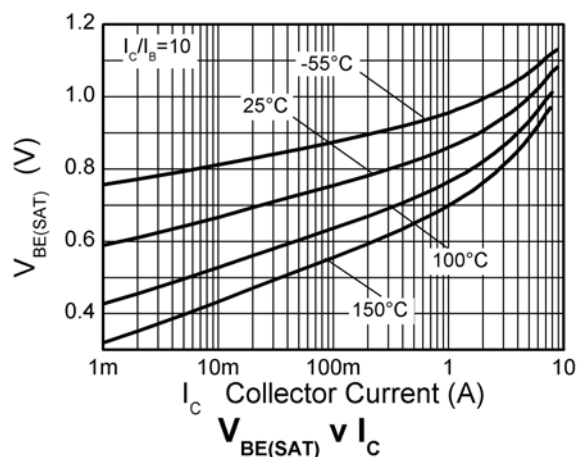
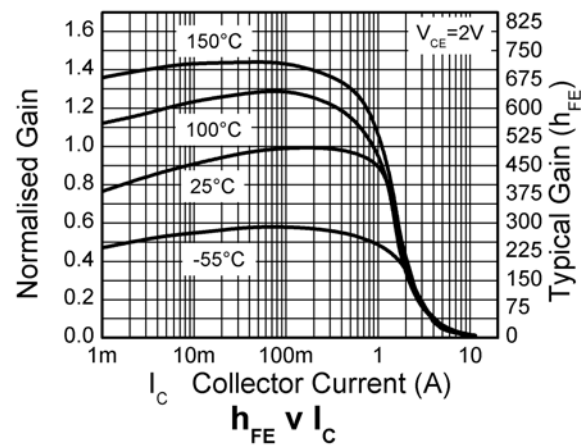
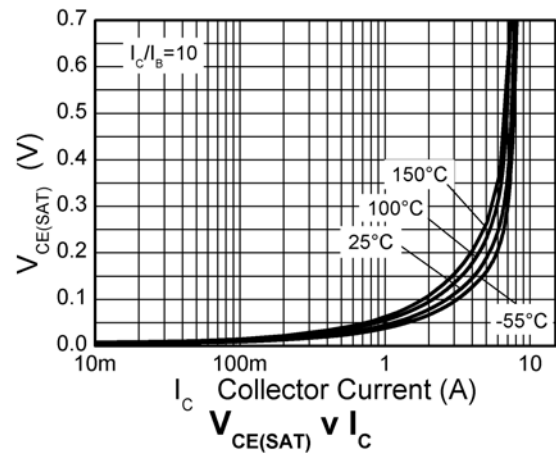
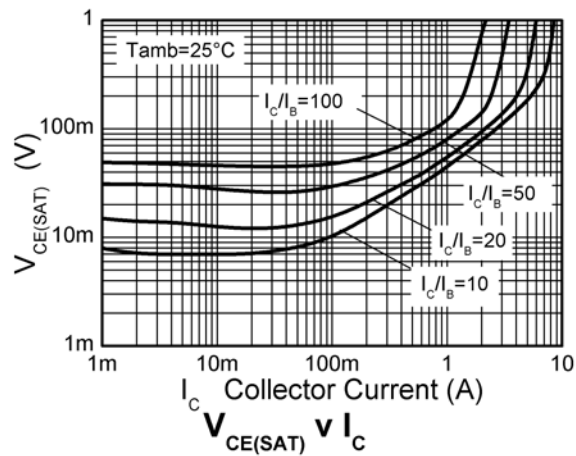
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	130	170		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	130	170		V	$I_C = 100\mu\text{A}$; $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	40	63		V	$I_C = 10\text{mA}^{(*)}$
Emitter-base breakdown voltage	BV_{EBO}	7	8.3		V	$I_E = 100\mu\text{A}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	7.4		V	$I_E = 100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	6	7.4		V	$I_E = 100\mu\text{A}$,
Collector-base cut-off current	I_{CBO}		<1	50 20	nA μA	$V_{CB} = 100\text{V}$ $V_{CB} = 100\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	I_{CEX}		-	100	nA	$V_{CE} = 100\text{V}$; $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter-base cut-off current	I_{EBO}		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		45	55	mV	$I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$
			120	210	mV	$I_C = 1\text{A}$, $I_B = 10\text{mA}^{(*)}$
			135	210	mV	$I_C = 2\text{A}$, $I_B = 40\text{mA}^{(*)}$
			140	190	mV	$I_C = 4\text{A}$, $I_B = 400\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		960	1050	mV	$I_C = 4\text{A}$, $I_B = 400\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		840	950	mV	$I_C = 4\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	300	450	900		$I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$
		300	450			$I_C = 1\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
		30	60			$I_C = 4\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
			10			$I_C = 10\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Transition frequency	f_T		190		MHz	$I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		11.7	20	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}^{(*)}$
Delay time	t_d		64		ns	$V_{CC} = 10\text{V}$, $I_C = 1\text{A}$, $I_{B1} = I_{B2} = 10\text{mA}$
Rise time	t_r		108		ns	
Storage time	t_s		428		ns	
Fall time	t_f		130		ns	

NOTES:

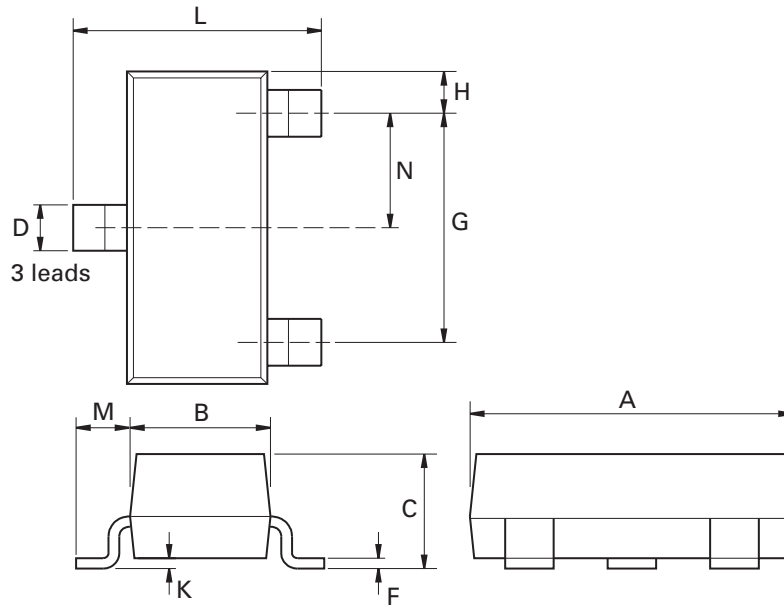
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTN25040DFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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